

## - 20V Dual P-Channel Enhancement Mode MOSFET

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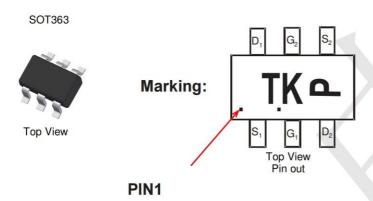
#### **Features**

- Fast switching
- Green Device Available
- Suit for 1.5V Gate Drive Applications

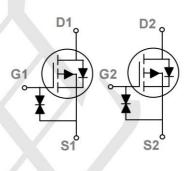
### **Application**

- Notebook
- Load Switch
- Networking
- Hand-held Instruments

## Package and Pin Configuration



### Circuit diagram



#### Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current – Continuous (T <sub>C</sub> =25°C)	-1.1	А
I <sub>DM</sub>	Drain Current – Pulsed1	-2.2	А
D	Power Dissipation (T <sub>C</sub> =25°C)	280	mVV
$P_D$	Power Dissipation – Derate above 25°C	2.5	mW/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

#### **Thermal Characteristics**

Symbol	pol Parameter		Max.	Unit
R <sub>0JA</sub>	Thermal Resistance Junction to ambient		350	°CM



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## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA		-20			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV <sub>DSS</sub> Temperature Coefficient Reference to 25°C , I <sub>D</sub> =-1mA			-0.01	/	V/°C
I <sub>DSS</sub>	Drain Source Leekage Current	V <sub>DS</sub> =-20V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C		( - /	-1	uA
	Drain-Source Leakage Current	V <sub>DS</sub> =-16V , V <sub>GS</sub> =0V , T <sub>J</sub> =125°C			-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm 12V$ , $V_{DS}=0V$		/	±20	uA

#### **On Characteristics**

		$V_{GS}$ =-4.5 $V$ , $I_D$ =-0.5 $A$	/	400		
		V <sub>GS</sub> =-2.5V , I <sub>D</sub> =-0.5A		550	680	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-1.8V , I <sub>D</sub> =-0.1A		750	1050	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	\/ -\/     - 250\	-0.5	-0.7	1.0	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS}=V_{DS}$ , $I_D=-250uA$	-	3		mV/°C

## **Dynamic and switching Characteristics**

Total Gate Charge <sup>2,3</sup>		<b>/</b> /	0.5		
Gate-Source Charge <sup>2, 3</sup>	$V_{DS}$ =10V , $V_{GS}$ =-4.5V , $I_{D}$ =-1 A	J	0.28		nC
Gate-Drain Charge <sup>2, 3</sup>			0.28		
Turn-On Delay Time <sup>2, 3</sup>			0.4		
Rise Time <sup>2, 3</sup>	$V_{DD}$ =-10V , $V_{GS}$ =-4.5V , $R_{G}$ =6 $\Omega$		0.06		20
Turn-Off Delay Time <sup>2, 3</sup>	I <sub>D</sub> =-1A		0.02		ns
Fall Time <sup>2,3</sup>			0.8		
Input Capacitance			55		-0
Output Capacitance	$V_{DS}$ =-10V , $V_{GS}$ =0V , F=1MHz		6		pF
Reverse Transfer Capacitance			4.5		
	Gate-Source Charge <sup>2,3</sup> Gate-Drain Charge <sup>2,3</sup> Turn-On Delay Time <sup>2,3</sup> Rise Time <sup>2,3</sup> Turn-Off Delay Time <sup>2,3</sup> Fall Time <sup>2,3</sup> Input Capacitance Output Capacitance	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$

## **Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =-0.2A , T <sub>J</sub> =25°C		-0.75	-1.1	V



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### **Characteristic Curves**

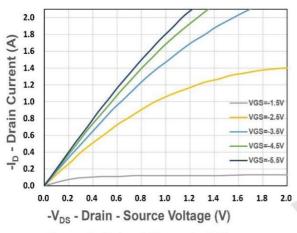


Figure 1. Output Characteristics

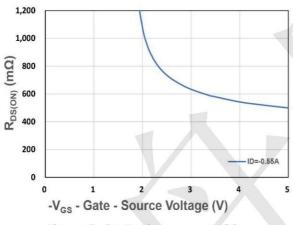


Figure 3. On-Resistance vs. VGS

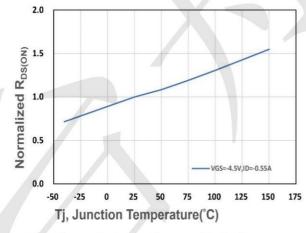


Figure 5. Drain-Source On Resistance

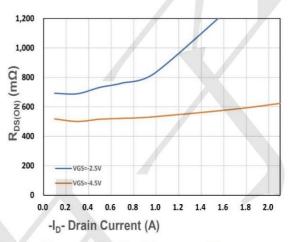


Figure 2. On-Resistance vs. ID

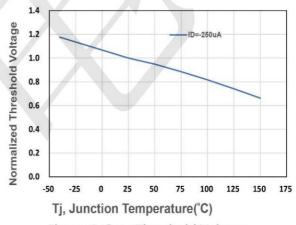


Figure 4. Gate Threshold Voltage

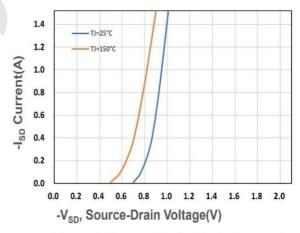
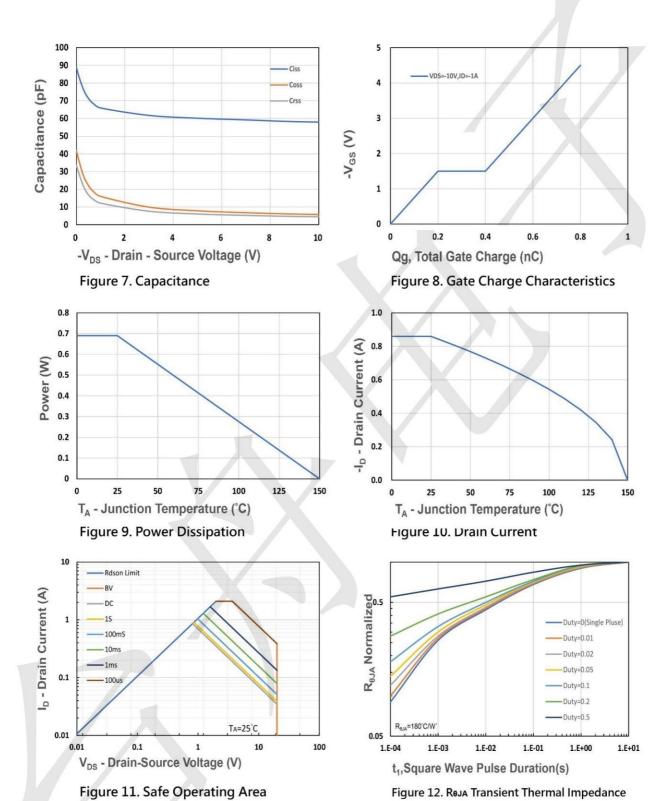


Figure 6. Source-Drain Diode Forward



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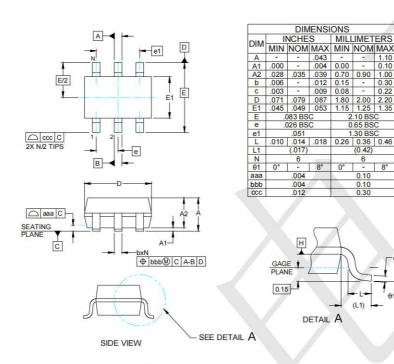
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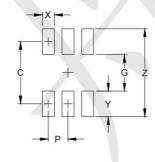


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# Outline Drawing - SOT-363(2.0X2.1)



## **Land Pattern - SOT-363**

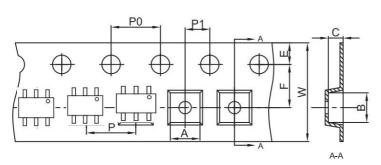


	DIMENSIONS								
DIM	<b>INCHES</b>	<b>MILLIMETERS</b>							
С	(.073)	(1.85)							
G	.039	1.00							
Р	.026	0.65							
X	.016	0.40							
Y	.033	0.85							
7	106	2 70							



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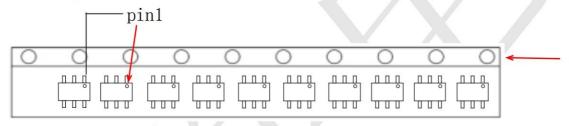
#### SOT-363 Embossed Carrier Tape



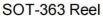
Dimensions are in millimeter										
Pkg type	А	В	С	d	E	F	P0	Р	P1	W
SOT-363	2.25	2.55	1.20	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

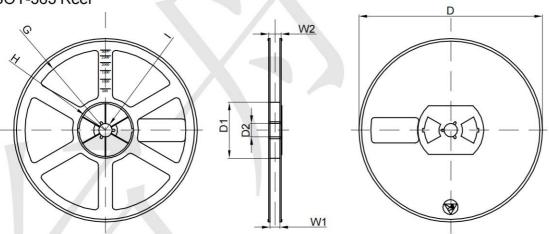
#### SOT-363 Tape Leader and Trailer

Package orientation in reel



Shipping:3000pcs / Tape & Reel





Dimensions are in millimeter									
Reel Option	D	D1	D2	G	Н	I	W1	W2	
7"Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30	

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	45,000 pcs	203×203×195	180,000 pcs	438×438×220	

## 单击下面可查看定价,库存,交付和生命周期等信息

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